

< High-power GaN HEMT (small signal gain stage) >

MGF0846G

L to C BAND / 40W non - matched

DESCRIPTION

The MGF0846G, GaN HEMT with an N-channel schottky gate, is designed for MMDS/UMTS/WiMAX applications.

FEATURES

- High voltage operation VDS=47V
- High output power Po=46.5dBm(TYP.) @f=2.6GHz,P3dB
- High efficiency ηd=60%(TYP.) @f=2.6GHz,P3dB
- Designed for use in Class AB linear amplifiers

APPLICATION

• MMDS/UMTS/WiMAX

QUALITY

• GG

Packaging

• 4 inch Tray (25 pcs)

RECOMMENDED BIAS CONDITIONS

• Vds=47V • Ids=340mA • Rg=30 Ω

Absolute maximum ratings (Ta=25°C)

| Symbol | Parameter | Ratings | Unit |
|--------|-------------------------|-------------|------|
| VDS | Drain to Source Voltage | 120 | V |
| VGS | Gate to source voltage | -10 | V |
| IGR | Reverse gate current | -6 | mA |
| IGF | Forward gate current | 120 | mΑ |
| PT*1 | Total power dissipation | 64 | W |
| Tch | Cannel temperature | 230 | °C |
| Tstg | Storage temperature | -65 to +175 | °C |

^{*1:}Tc=25°C

OUTLINE DRAWING Unit: millimeters Outline DRAWING Unit: millimeters Outline DRAWING Unit: millimeters Outline DRAWING Outline DRAWING

Electrical characteristics (Ta=25°C)

| Symbol | Parameter | Test conditions | | Limits | | |
|--------------|--------------------------------|--------------------------|------|--------|------|------|
| | | | Min. | Тур. | Max. | |
| VGS(off) | Gate to source cut-off voltage | VDS=47V,ID=12mA | -1 | - | -5 | V |
| P3dB | 3dB gain compression power | VDS=47V,ID(RF off)=340mA | 45.5 | 46.5 | - | dBm |
| P1dB | 1dB gain compression power | f=2.6GHz | - | 45.5 | - | dBm |
| ηd *2 | Drain efficiency | *2 : @P3dB | - | 60 | - | % |
| GLP *3 | Linear power gain | *3 : Pin=20dBm | 12 | 13 | - | dB |
| Rth(ch-c) *4 | Thermal resistance | ∆ Vf method | - | 2.5 | 3.2 | °C/W |

^{*4 :}Channel-case

Specification are subject to change without notice.

Note

DC aging is recommended to perform before operating in order to stabilize a characteristics of GaN-HEMT. (Ta≧80°C)

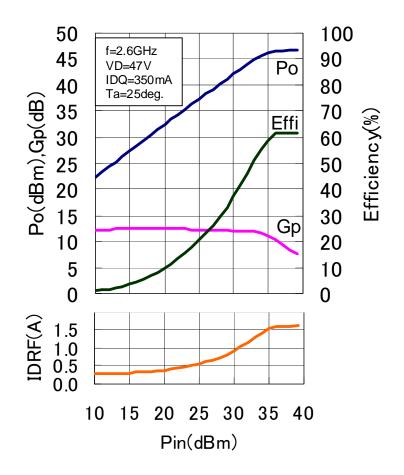
- Bias conditions Vds=47V , Ids=340mA
- Time 10hrs

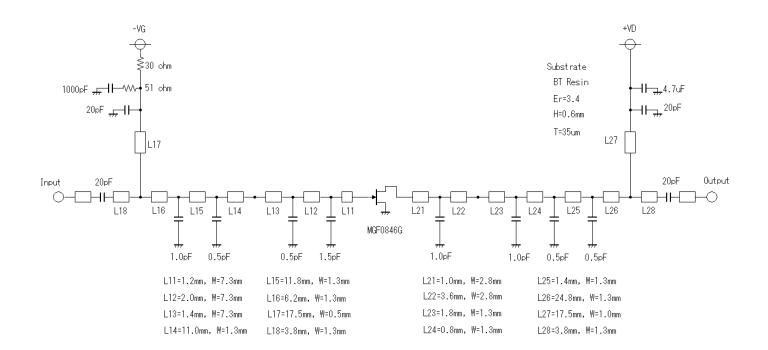
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MGF0846G Example of Circuit Schematic and Charactreistics: f = 2.6 GHz





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 $\textbf{MGF0846G S-parameters}(\ \texttt{Ta=25deg.C}\ ,\ \texttt{VDS=47(V)}, \texttt{IDS=350(mA)}\)$

| f (GHz) | S Parameters(Typ.) | | | | | | | |
|------------|--------------------|-------------|-------|-------------|-------|-------------|-------|-------------|
| | S11 | | S21 | | S12 | | S22 | |
| | Magn. | Angle(deg.) | Magn. | Angle(deg.) | Magn. | Angle(deg.) | Magn. | Angle(deg.) |
| 0.6 | 0.966 | -173.6 | 5.549 | 85.5 | 0.029 | 30.5 | 0.660 | -173.7 |
| 1.0 | 0.910 | -176.4 | 3.379 | 74.4 | 0.028 | 3.6 | 0.643 | -179.5 |
| 1.4 | 0.893 | 176.6 | 2.433 | 66.6 | 0.027 | 9.1 | 0.632 | 178.5 |
| 1.8 | 0.903 | 174.0 | 1.992 | 59.5 | 0.029 | 6.7 | 0.632 | 178.4 |
| 2.2 | 0.897 | 168.3 | 1.675 | 52.0 | 0.033 | -1.2 | 0.648 | 175.2 |
| 2.6 | 0.909 | 163.9 | 1.402 | 42.0 | 0.026 | 4.1 | 0.664 | 173.0 |
| 3.0 | 0.875 | 157.0 | 1.293 | 34.7 | 0.031 | -1.7 | 0.628 | 168.0 |
| 3.4 | 0.905 | 151.1 | 1.206 | 25.6 | 0.034 | 11.6 | 0.635 | 162.8 |
| 3.8 | 0.894 | 144.3 | 1.051 | 15.3 | 0.048 | 1.3 | 0.644 | 158.0 |
| 4.2 | 0.907 | 140.7 | 0.945 | 7.4 | 0.036 | -19.0 | 0.666 | 152.3 |
| 4.6 | 0.911 | 136.7 | 0.853 | 1.2 | 0.038 | -22.2 | 0.682 | 147.7 |
| 5.0 | 0.908 | 134.5 | 0.793 | -4.8 | 0.035 | -5.2 | 0.702 | 144.5 |
| 5.4 | 0.901 | 130.9 | 0.728 | -10.9 | 0.039 | -3.8 | 0.715 | 142.1 |
| 5.8 | 0.894 | 126.8 | 0.695 | -18.1 | 0.041 | -9.1 | 0.740 | 139.3 |
| 6.2 | 0.891 | 119.4 | 0.658 | -25.5 | 0.046 | -12.4 | 0.742 | 137.2 |
| 6.6 | 0.887 | 110.9 | 0.630 | -33.8 | 0.049 | -14.7 | 0.751 | 133.2 |
| 7.0 | 0.894 | 99.5 | 0.600 | -43.6 | 0.049 | -22.0 | 0.735 | 127.9 |
| 7.4 | 0.899 | 91.5 | 0.570 | -51.5 | 0.056 | -25.4 | 0.731 | 120.9 |
| 7.8 | 0.902 | 83.8 | 0.530 | -60.5 | 0.052 | -32.9 | 0.733 | 113.1 |
| 8.2 | 0.906 | 78.8 | 0.500 | -68.5 | 0.058 | -36.3 | 0.756 | 103.9 |

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